

REMARKS

No new matter has been added. The Applicants again request entry of the amendments as set forth in the Appendices hereto prior to examination of the application on the merits.

Respectfully submitted,



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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE SPECIFICATION:

Please replace paragraph [0001] with the following:

[0001] Cross Reference to Related [Application] Applications: This application is a continuation of application Serial No. 09/518,293, filed March 3, 2000, [pending] now U.S. Patent 6,287,942, issued September 11, 2001, which is a continuation of application Serial No. 09/244,733, filed February 5, 1999, now U.S. Patent 6,084,288, issued July 4, 2000, which is continuation of application Serial No. 08/910,613, filed August 13, 1997, now U.S. Patent 5,903,044, issued May 11, 1999, which is a continuation of application Serial No. 08/614,178, filed March 12, 1996, now U.S. Patent 5,682,065, issued October 28, 1997.

IN THE CLAIMS:

1. (Amended) A sealing method for at least one semiconductor device on a first side of a wafer substrate, the wafer substrate having [a] the first side, a second side, and a thickness, the at least one semiconductor device having a plurality of sides and at least one bond pad thereon, said sealing method comprising:
reducing the thickness of at least a portion of the wafer substrate from the second side thereof;
coating the first side of the wafer substrate using a first coating to substantially seal the at least one semiconductor device [formed] on the first side of the wafer substrate;
removing a portion of the wafer substrate from each of the plurality of sides [side] of the at least one semiconductor device [formed] on the first side of the wafer substrate, the portion of the wafer substrate being removed extending from the second side of the wafer substrate to the coating on the first side of the wafer substrate;
coating the second side of the wafer substrate using a second coating to substantially seal the second side of the wafer substrate and to substantially seal the plurality of sides of the at least one semiconductor device;

removing a portion of the first coating on the first side of the wafer substrate for uncovering a portion of the at least one bond pad located on the at least one semiconductor device; and applying a third coating to the at least one bond pad of the at least one semiconductor device, the third coating substantially sealingly engaging the at least one bond pad and substantially sealing the first coating.

6. (Amended) A sealing method for at least one semiconductor device on a first side of a wafer substrate, the wafer substrate having [a] the first side, a second side, and a thickness, the at least one semiconductor device having a plurality of sides and at least one bond pad thereon, said sealing method comprising:

coating the first side of the wafer substrate with a first coating to substantially seal the at least one semiconductor device [formed] on the first side of the wafer substrate;
reducing the thickness of at least a portion of the wafer substrate from the second side thereof by thinning the wafer substrate in at least the portion of the wafer substrate located on said at least one semiconductor device;
removing a portion of the wafer substrate from each [side] of the plurality of sides of the at least one semiconductor device [formed] on the wafer substrate by removing a portion of the wafer substrate extending through the thickness thereof; and
coating the second side of the wafer substrate with a second coating.

8. (Amended) The method of claim 7, wherein the removing the portion of the wafer substrate includes:
etching the wafer substrate from each side of the plurality of sides of the at least one semiconductor device [formed] on the wafer substrate, the portion of the wafer substrate removed from said each side of the plurality of sides of the at least one semiconductor device substantially extending from the second side of the wafer substrate to substantially the first coating on the first side of the wafer substrate through the thickness thereof.

19. (Amended) The method of claim 18, further comprising:
etching portions of the fifth coating on the first side of the wafer substrate, leaving portions of the
fifth coating remaining on the first side of the wafer substrate in predetermined areas of
the wafer substrate.

20. (Amended) The method of claim 19, further comprising:
removing substantially the sixth coating from the first side of the wafer substrate, uncovering
predetermined remaining portions of the fifth coating on the first side of the wafer
substrate.